

# PATENT ABSTRACTS OF JAPAN

(11)Publication number : 07-070752

(43)Date of publication of application : 14.03.1995

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(51)Int.Cl. C23C 16/40  
H01B 1/08  
H01B 12/06  
H01B 13/00

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(21)Application number : 05-217266

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(22)Date of filing : 01.09.1993

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## (54) FILM FORMING METHOD OF OXIDE SUPERCONDUCTOR

### (57)Abstract:

PURPOSE: To improve the smoothness of a film and improve crystallizability in the atomic layer epitaxy film forming.

CONSTITUTION: In the film forming method of the oxide superconductor forming the atomic layer epitaxy film of the oxide superconductor consisting of the compd. containing more than three component metal element, the process in which plural metal elements constituting of one part of an unit lattice is laminated simultaneously as one unit is included. In the film forming method of  $R\text{Ba}_2\text{Cu}_3\text{O}_{7-\delta}$  (R is either one among Y, La, Pr, Nd, Sm, Eu, Gd, Dy, Ho, Er and Yb), the simultaneously laminating process of Cu, R and Cu as a subunit in order of Ba/Cu, R and Cu/Ba/Cu is included.

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## LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the  
examiner's decision of rejection or application  
converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of  
rejection]

[Date of requesting appeal against examiner's decision  
of rejection]

[Date of extinction of right]